

3CD5,3CD6**PNP Silicon Low Frequency High Power Transistor****Features:**

1. Heavy output current.Small saturation voltage drop. Good temperature stability.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for power amplify, Low-speed switch, power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications							
			3CD5				3CD6			
			A	B	C	D	E	F	G	H
Collector-Emitter Voltage	V_{CEO}	V	30	50	80	110	150	200	250	300
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	30	50	80	110	150	200	250	300
Emitter-Base Voltage	V_{EBO}	V	4				4			
Max. Collector Current	I_{CM}	A	3				5			
Max. Collector Dissipation	P_{CM}	W	30 (Tc≤75°C)				50 (Tc≤75°C)			
Junction Temperature	T_{jm}	°C	175							
Storage Temperature	T_{stg}	°C	-55~+175							
Collector-Emitter Leakage Current	I_{CEO}	mA	2 (V _{CE} =20V)							
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.5 (A~E: I _C =1.5A, I _B =0.3A; F~H: I _C =1.0A, I _B =0.2A)				1.5 (A~E: I _C =2.5A, I _B =0.5A; F~H: I _C =1.0A, I _B =0.2A)			
DC Current Gain	h_{FE}		Max.:240, Min.:15 (A~E: V _{CE} =10V, I _C =1.5A; F~H:V _{CE} =10V, I _C =1.0A)				Max.:240, Min.:15 (A~E: V _{CE} =10V, I _C =2.5A; F~H:V _{CE} =10V, I _C =1.0A)			
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	≥4 (I _E =3mA)							

h_{FE} Colored:

Color	Red	Orange	Yellow	Green	Blue	Purple
h_{FE}	15~25	25~40	40~55	55~80	80~120	120~240

Outline and Dimensions: